

AMENDMENT TO THE CLAIMS

Please amend the claims without prejudice, without admission, without surrender of subject matter, and without any intention of creating any estoppel as to equivalents, as follows.

In the Claims:

1. (Currently amended) A dielectric particle aggregate made of dielectric particles of BaO-TiO₂-Nd₂O₃ type dielectric or SrTiO₃ type dielectric, wherein each of the particles contain ZnTiO₃ and/or Zn₂TiO₄ in the surface layer thereof.

Claims 2-3 (Canceled)

4. (Previously presented) The dielectric particle aggregate as claimed in claim 1, wherein the BaO-TiO₂-Nd₂O₃ type dielectric contains as principal ingredients BaO by 10 to 16 mol%, TiO₂ by 67 to 72 mol% and Nd₂O₃ by 16 to 18 mol% and as auxiliary ingredients Bi₂O₃ by 7 to 10 parts by weight and Al₂O₃ by 0.3 to 1.0 parts by weight relative to 100 parts by weight of the principal ingredients.

5. (Previously presented) The dielectric particle aggregate as claimed in claim 1, wherein the surface layer has a thickness not greater than 50 nm.

6. (Previously presented) The dielectric particle aggregate as claimed in claim 1, wherein the dielectric particle aggregate has an average particle size of 0.4 μm to 3.0 μm.

7. (Previously presented) A method of manufacturing a dielectric particle aggregate as claimed in claim 1, comprising the steps of mixing ZnO with an aggregate of particles of a dielectric base material containing Ti and subjecting the resultant mixture to a calcining process.

8. (Original) The method of manufacturing dielectric particle aggregate as claimed in claim 7, wherein 0.5 to 10 parts by weight of ZnO is mixed with 100 parts by weight of the aggregate of particles of dielectric base material.

9. (Previously presented) The method of manufacturing dielectric particle aggregate as claimed in claim 7, wherein the calcining process is conducted in an oxygen-containing atmosphere.

10. (Previously presented) The method of manufacturing dielectric particle aggregate as claimed in claim 7, wherein the temperature of the-TiO process is 900 to 1,200°C.

11. (Previously Presented) A low temperature sinterable dielectric ceramic composition containing the dielectric particle aggregate as claimed in claim 1 by 100 parts by weight and a glass component by 2.5 to 20 parts by weight.

12. (Original) The low temperature sinterable dielectric ceramic composition as claimed in claim 11, wherein the glass component contains ZnO by 45 to 70 wt%, B₂O₃ by 5 to 13 wt%, SiO₂ by 7 to 40 wt% and Al₂O₃ by 8 to 20 wt%.

13. (Withdrawn) A low-temperature-sintered dielectric ceramic containing 100 parts by weight of dielectric particles constituting the dielectric particle aggregate as claimed in claim 1 and 2.5 to 20 parts by weight of glass component.

14. (Withdrawn) The low-temperature-sintered dielectric ceramic as claimed in claim 13, wherein the glass component contains ZnO by 45 to 70 wt%, B₂O₃ by 5 to 13 wt%, SiO₂ by 7 to 40 wt% and Al₂O₃ by 8 to 20 wt%.

15. (Withdrawn) A method of manufacturing a low-temperature-sintered dielectric ceramic comprising the step of sintering the low temperature sinterable dielectric ceramic composition as claimed in claim 11 at 880 to 1,000°C.

16. (Withdrawn) The method of manufacturing low-temperature-sintered dielectric ceramic as claimed in claim 15, wherein the glass component contains ZnO by 45 to 70 wt%, B₂O₃ by 5 to 13 wt%, SiO₂ by 7 to 40 wt% and Al₂O₃ by 8 to 20 wt%.

17. (Withdrawn) The method of manufacturing low-temperature-sintered dielectric ceramic as claimed in claim 15, wherein the sintering step is conducted on a laminate having a layer containing the low temperature sinterable dielectric ceramic composition and a layer containing metal to thereby obtain an electronic part having a laminated structure where the metal layer functions as an internal conductor.

18. (Withdrawn) The method of manufacturing low-temperature-sintered dielectric ceramic as claimed in claim 17, wherein the metal layer is made of Ag, Cu or an alloy containing at least either of them.

19. (New) The dielectric particle aggregate as claimed in claim 1, wherein ZnTiO_3 and/or Zn_2TiO_4 is contained only in the surface layer of the particles.

20. (New) The dielectric particle aggregate as claimed in claim 5, wherein the surface layer has a thickness not less than 10 nm.

21. (New) The method of manufacturing low-temperature-sintered dielectric ceramic as claimed in claim 7, wherein the particles of dielectric base material practically do not contain Zn.

22. (New) The method of manufacturing low-temperature-sintered dielectric ceramic as claimed in claim 7, wherein ZnTiO_3 and/or Zn_2TiO_4 is formed on the surface of the particles of dielectric base material in the calcining process.